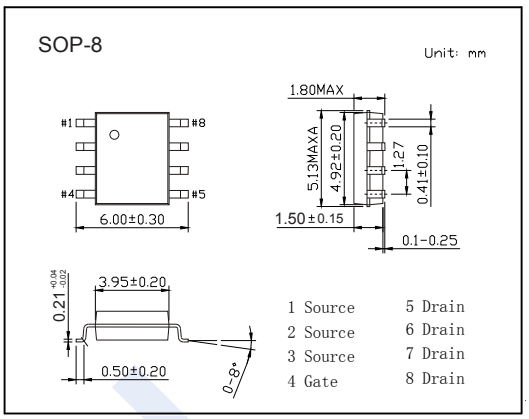
P-Channel MOSFET
KI10P40DY

■ Features

- V_{DS}=-40V
- I_D =-15A
- $R_{DS(on)}$= 42mΩ@V_{GS}=-10V ,I_D=-1A
- $R_{DS(on)}$= 70mΩ@V_{GS}=-4.5V,I_D=-1A



■ Absolute Maximum Ratings Ta = 25℃

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-40	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current	TA=25℃	I_D	-15	A
	TA=70℃		-10	
Pulsed Drain Current		I_{DM}	-30	
Power Dissipation	TA=25℃	P_D	1.3	W
	TA=70℃		0.8	
Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	I_D=-250μA, V_{GS}=0V	-40			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-32V, V_{GS}=0V,T_J=25℃			-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} , I_D=-250μA	1		3	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-1A			42	mΩ
		V_{GS}=-10V, I_D=-10A			45	
		V_{GS}=-4.5V, I_D=-1A			70	

■ Marking

Marking	10P40 KC****